

# MA2SV03

Silicon epitaxial planar type

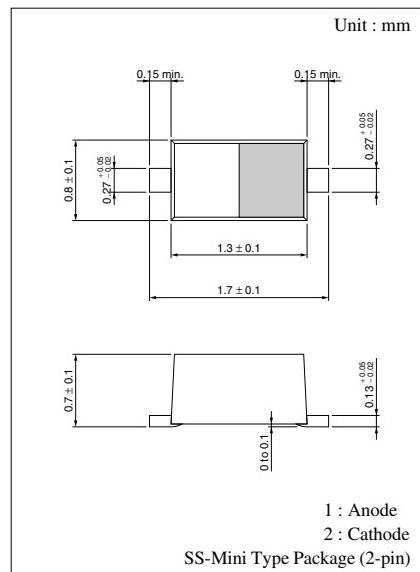
For VCO

## ■ Features

- Good linearity and large capacitance-ratio in  $C_D$  —  $V_R$  relation
- Small series resistance  $r_D$
- SS-mini type package, allowing downsizing of equipment and automatic insertion through the taping package

## ■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Reverse voltage (DC)	$V_R$	6	V
Junction temperature	$T_j$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$



Marking Symbol: 4

## ■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse current (DC)	$I_R$	$V_R = 5 \text{ V}$			10	nA
Diode capacitance	$C_{D(IV)}$	$V_R = 1 \text{ V}, f = 1 \text{ MHz}$	5.20		5.80	pF
	$C_{D(4V)}$	$V_R = 4 \text{ V}, f = 1 \text{ MHz}$	2.10		2.58	pF
Capacitance ratio	$C_{D(IV)}/C_{D(4V)}$		2.1		2.6	—
Series resistance*	$r_D$	$V_R = 4 \text{ V}, f = 470 \text{ MHz}$			0.3	$\Omega$

Note) 1. Rated input/output frequency: 470 MHz

2. \* :  $r_f$  measuring instrument: YHP MODEL 4191A RF IMPEDANCE ANALYZER

